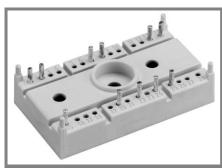
## **SK 70 WT**



# SEMITOP® 3

### **Thyristor**

#### **SK 70 WT**

**Target Data** 

#### **Features**

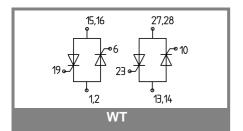
- Compact Design
- · One screw mounting
- Heat transfer and isolation trough direct copper bonded aluminium oxide ceramic (DCB)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

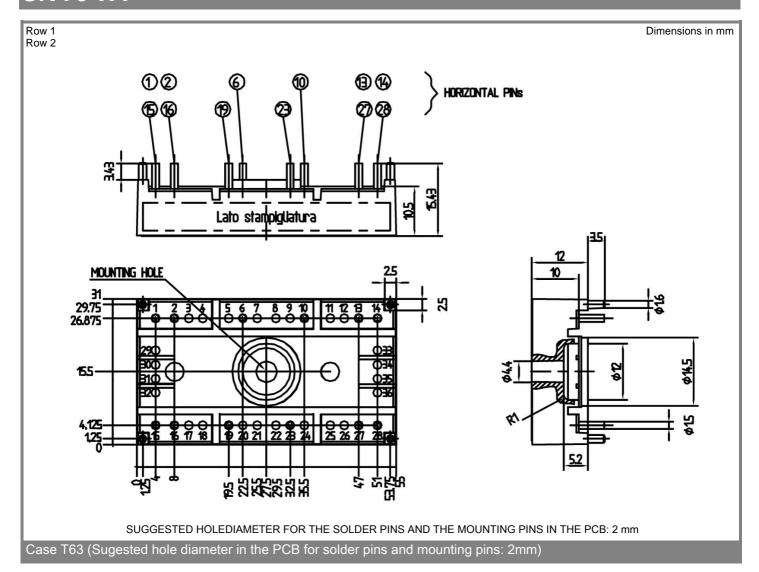
### **Typical Applications**

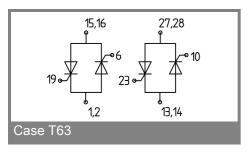
- Soft starters
- Light control (studios, theaters...)
- Temperature control

V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub> V	I <sub>RMS</sub> = 72 A (T <sub>s</sub> = 85 °C)
900	800	SK 70 WT 08
1300	1200	SK 70 WT 12
1700	1600	SK 70 WT 16

Characteristics					
Symbol	Conditions	Values	Units		
I <sub>D</sub>			Α		
$I_{TAV}/I_{FAV}$			Α		
I <sub>RMS</sub>	per phase		А		
I <sub>TSM</sub> /I <sub>FSM</sub>	T <sub>vi</sub> = 25 (125) °C; 10 ms	1000 (900)	Α		
l²t	T <sub>vj</sub> = 25 (125) °C; 8,3 10 ms	5000 (4000)	A²s		
T <sub>stg</sub>		-40 +125	°C		
T <sub>solder</sub>	terminals, 10 s	260	°C		
Thyristor	•				
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	1000	V/µs		
(di/dt) <sub>cr</sub>	$T_{vi} = 125 ^{\circ}\text{C}; f = f = 5060 \text{Hz}$	50	A/µs		
t <sub>q</sub>	$T_{vi} = 125 ^{\circ}\text{C}$ ; typ.	80	μs		
I <sub>H</sub>	T <sub>vi</sub> = 25 °C; typ. / max.	100 / 200	mA		
IL	$T_{vi} = 25 ^{\circ}\text{C};  R_{G} = 33  \Omega;  \text{typ. / max.}$	200 / 400	mA		
V <sub>T</sub>	$T_{vi} = 25 ^{\circ}\text{C}; (I_T = 120 \text{A}); \text{max}.$	1,8	V		
V <sub>T(TO)</sub>	T <sub>vi</sub> = 125 °C	max. 1	V		
r <sub>T</sub>	$T_{vi}^{-3} = 125  ^{\circ}\text{C}$	max. 6	mΩ		
I <sub>DD</sub> ; I <sub>RD</sub>	$T_{vj}^{-1}$ = 125 °C; $V_{DD} = V_{DRM}$ ; $V_{RD} = V_{RRM}$	max. 15	mA		
R <sub>th(j-s)</sub>	per thyristor	0,8	K/W		
T <sub>vi</sub>		- 40 + 125	°C		
V <sub>GT</sub>	$T_{vi} = 25 ^{\circ}\text{C}; \text{d.c.}$	2	V		
I <sub>GT</sub>	$T_{vi}^{'j} = 25  ^{\circ}\text{C}; \text{d.c.}$	100	mA		
V <sub>GD</sub>	$T_{vi}^{yj}$ = 125 °C; d.c.	0,25	V		
I <sub>GD</sub>	T <sub>vi</sub> = 125 °C; d.c.	5	mA		
Diode	1	1			
$V_{F}$	$T_{vi} = {^{\circ}C}; (I_F = A); max.$		V		
V <sub>(TO)</sub>	$T_{vi}^{yj} = {^{\circ}C}$		V		
r <sub>T</sub>	$T_{vi}^{'j} = {}^{\circ}C$		mΩ		
I <sub>RD</sub>	$T_{vj} = {^{\circ}C}; V_{RD} = V_{RRM}$		mA		
R <sub>th(j-s)</sub>	,		K/W		
T <sub>vi</sub>			°C		
Mechanic	al data				
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min	2500 (3000)	V		
M <sub>1</sub>	mounting torque	2,5	Nm		
w	- ,	30	g		
Case	SEMITOP® 3	T 63			







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.